

# Octal 3-State Noninverting D Flip-Flop High-Performance Silicon-Gate CMOS

The MC54/74HC374A is identical in pinout to the LS374. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

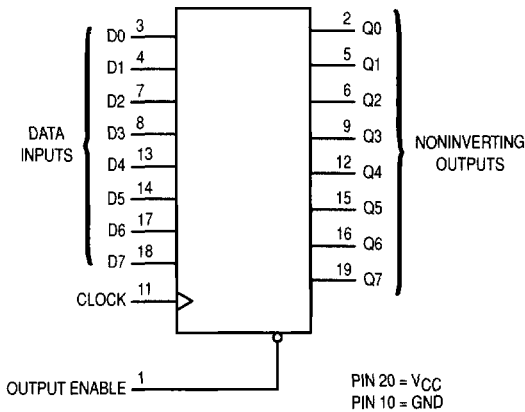
Data meeting the setup time is clocked to the outputs with the rising edge of the clock. The Output Enable input does not affect the states of the flip-flops, but when Output Enable is high, the outputs are forced to the high-impedance state; thus, data may be stored even when the outputs are not enabled.

The HC374A is identical in function to the HC574A which has the input pins on the opposite side of the package from the output. This device is similar in function to the HC534A which has inverting outputs.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0  $\mu$ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 266 FETs or 66.5 Equivalent Gates

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### LOGIC DIAGRAM



### FUNCTION TABLE

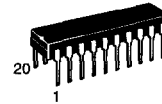
Inputs			Output
Output Enable	Clock	D	Q
L	$\nearrow$	H	H
L	$\nearrow$	L	L
L	L,H, $\sim$	X	No Change
H	X	X	Z

X = don't care  
Z = high impedance

## MC54/74HC374A



**J SUFFIX**  
CERAMIC PACKAGE  
CASE 732-03



**N SUFFIX**  
PLASTIC PACKAGE  
CASE 738-03



**DW SUFFIX**  
SOIC PACKAGE  
CASE 751D-04



**SD SUFFIX**  
SSOP PACKAGE  
CASE 940C-03



**DT SUFFIX**  
TSSOP PACKAGE  
CASE 948E-02

### ORDERING INFORMATION

MC54HCXXXAJ	Ceramic
MC74HCXXXAN	Plastic
MC74HCXXXADW	SOIC
MC74HCXXXASD	SSOP
MC74HCXXXADT	TSSOP

### PIN ASSIGNMENT

OUTPUT ENABLE	1	20	V <sub>CC</sub>
Q0	2	19	Q7
D0	3	18	D7
D1	4	17	D6
Q1	5	16	Q6
Q2	6	15	Q5
D2	7	14	D5
D3	8	13	D4
Q3	9	12	Q4
GND	10	11	CLOCK



## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 1.5 to V <sub>CC</sub> + 1.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 35	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package† SSOP or TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package) (Ceramic DIP)	260 300	°C

\* Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

† Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C  
Ceramic DIP: - 10 mW/°C from 100° to 125°C  
SOIC Package: - 7 mW/°C from 65° to 125°C  
SSOP or TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V	
T <sub>A</sub>	Operating Temperature, All Package Types	- 55	+ 125	°C	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	0 0 0	1000 500 400	ns

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit		
				- 55 to 25°C	≤ 85°C	≤ 125°C			
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V  I <sub>out</sub>   ≤ 20 μA	2.0	1.50	1.50	1.50	V		
			4.5	3.15	3.15	3.15			
			6.0	4.20	4.20	4.20			
V <sub>IL</sub>	Maximum Low-Level Input Voltage	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V  I <sub>out</sub>   ≤ 20 μA	2.0	0.50	0.50	0.50	V		
			4.5	1.35	1.35	1.35			
			6.0	1.80	1.80	1.80			
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20 μA	2.0	1.90	1.90	1.90	V		
			4.5	4.40	4.40	4.40			
			6.0	5.90	5.90	5.90			
			4.5	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 6.0 mA  I <sub>out</sub>   ≤ 7.8 mA	3.98	3.84	3.70	V	
					6.0	5.48	5.34		5.20

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**DC ELECTRICAL CHARACTERISTICS** (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20 μA	2.0	0.10	0.10	0.10	V
			4.5 6.0	0.10 0.10	0.10 0.10	0.10 0.10	
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 6.0 mA  I <sub>out</sub>   ≤ 7.8 mA	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	V
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I <sub>OZ</sub>	Maximum Three-State Leakage Current	Output in High-Impedance State V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>out</sub> = V <sub>CC</sub> or GND	6.0	± 0.5	± 5.0	± 10	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0 μA	6.0	4	40	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2.

**SWITCHING WAVEFORMS**

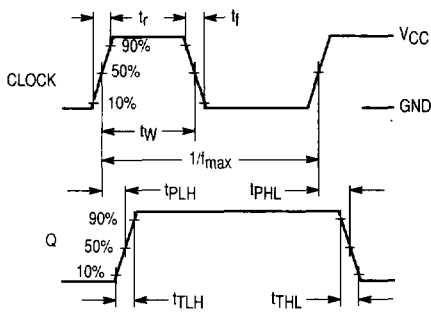


Figure 1.

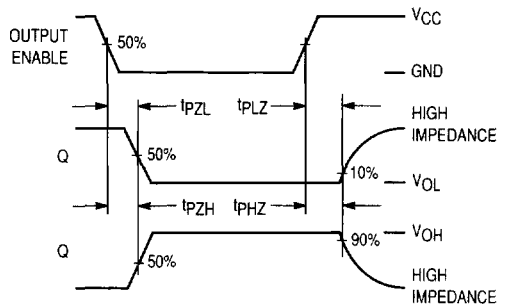


Figure 2.

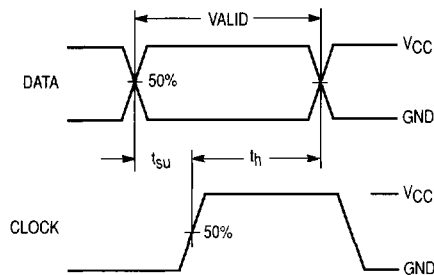
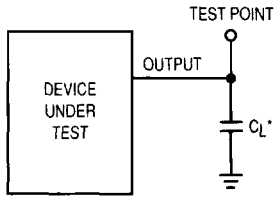


Figure 3.

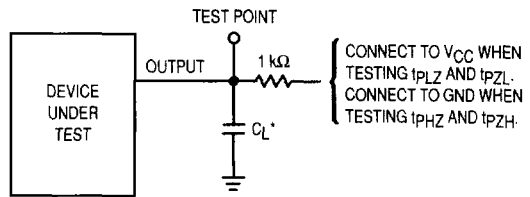
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TEST CIRCUITS



\* Includes all probe and jig capacitance

Figure 4.



\* Includes all probe and jig capacitance

Figure 5.